

ABSTRACT OF THE DISCLOSURE

A ferroelectric capacitor and a method for manufacturing the same includes a lower electrode, a dielectric layer, and an upper electrode layer, which are sequentially stacked, wherein the dielectric layer has a multi-layer structure including a plurality of sequentially stacked ferroelectric films, and wherein two adjacent ferroelectric films have either different compositions or different composition ratios. Use of a ferroelectric capacitor according to an embodiment of the present invention, it is possible to hold stable polarization states of ferroelectric domains for a long retention time, and thus data written in the ferroelectric capacitor a long time ago can be accurately written, thereby improving the reliability of a ferroelectric random access memory (FRAM).